Silicon Carbide Schottky Diode

1200 V, 10 A

FFSB10120A-F085

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 100 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- AEC-Q101 qualified

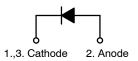
Applications

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

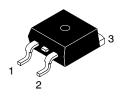


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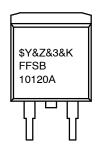


Schottky Diode



D²PAK2 (TO-263-2L) CASE 418BK

MARKING DIAGRAM



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code = Numeric Date Code &3 = Lot Code

&K

FFSB10120A = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FFSB10120A-F085

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter		Ratings	Unit
V _{RRM}	Peak Repetitive Reverse Voltage		1200	V
E _{AS}	Single Pulse Avalanche Energy (Note 1)		100	mJ
I _F	Continuous Rectified Forward Current @ T _C < 164°C Continuous Rectified Forward Current @ T _C < 135°C		10	Α
			21	
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	850	Α
		T _C = 150°C, 10 μs	800	
I _{F, SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, tp = 8.3 ms	90	Α
I _{F, RM}	Repetitive Forward Surge Current	Half-Sine Pulse, tp = 8.3 ms	35	Α
Ptot	Power Dissipation	T _C = 25°C	283	W
		T _C = 150°C	47	W
T _J , T _{STG}	Operating and Storage Temperature Range TO247 Mounting Torque, M3 Screw		-55 to +175	°C
			60	Ncm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.53	°C/W

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Shipping [†]
FFSB10120A-F085	FFSB10120A	D2PAK	800 Units/ Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

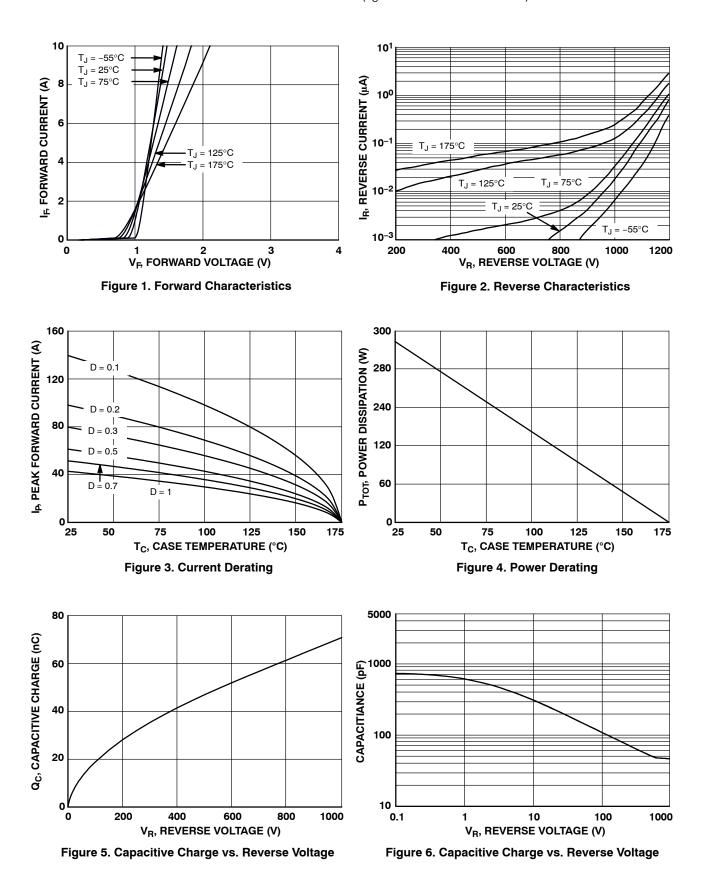
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Unit
V _F	Forward Voltage	I _F = 10 A, T _C = 25°C	-	1.45	1.75	V
		I _F = 10 A, T _C = 125°C	-	1.7	2	
		I _F = 10 A, T _C = 175°C	-	2	2.4	
I _R	Reverse Current	V _R = 1200 V, T _C = 25°C	-	-	200	μΑ
		V _R = 1200 V, T _C = 125°C	-	-	300	
		V _R = 1200 V, T _C = 175°C	-	-	400	
Q _C	Total Capacitive Charge	V = 800 V	-	62	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	612	-	pF
		V _R = 400 V, f = 100 kHz	-	58	-	
		V _R = 800 V, f = 100 kHz	-	47	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. E_{AS} of 100 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 20 A, V = 50 V.

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TYPICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)



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TYPICAL CHARACTERISTICS ($T_C = 25$ °C unless otherwise noted) (continued)

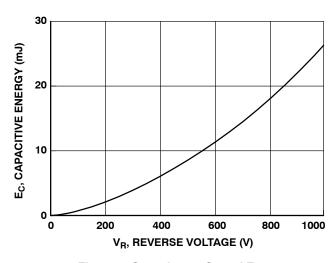


Figure 7. Capacitance Stored Energy

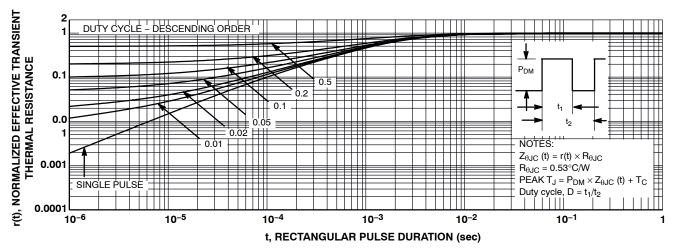


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

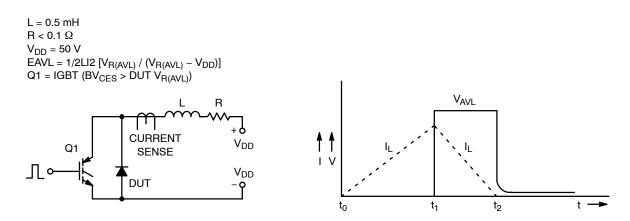
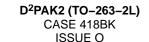
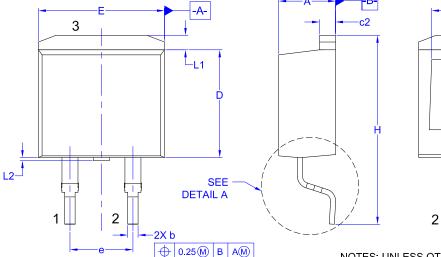
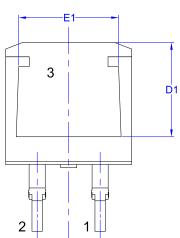


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform



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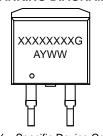


NOTES: UNLESS OTHERWISE SPECIFIED

- A) ALL DIMENSIONS ARE IN MILLIMETERS.
 B) REFERENCE JEDEC, TO-263, VARIATION AB.
- C) DIMENSIONING AND TOLERANCING PER
 DIMENSIONING AND TOLERANCING PER
- ASME Y14.5 2009.
 D) LANDPATTERN RECOMMENDATION PER IPC
- D) LANDPATTERN RECOMMENDATION PER IPO TO254P1524X482-3N

DETAIL A, ROTATED 90°	B)
SCALE: 2X	'(
GAUGE PLANE	D)
M	L3
B 0.10 SEATING —	-A1
GENERIC PLANE	—10.67—— -

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code

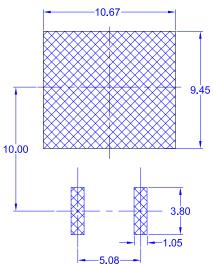
A = Assembly Location

Y = Year

WW = Work Week

G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.



LAND PATTERN RECOMMENDATION
UNLESS NOTED. ALL DIMS TYPICAL

MIN	NOM	MAX	
4.06	4.57	4.83	
0.00	0.10	0.25	
0.51	0.81	0.99	
0.30	0.407	0.74	
1.14	1.30	1.65	
8.38	8.69	9.65	
7.30	7.80	8.30	
9.65	10.16	10.67	
8.00	8.62	9.00	
5.08 BSC			
14.60	15.35	15.88	
1.78	2.54	2.79	
0.90	1.29	1.68	
0.00	0.15	0.25	
0.25 BSC			
0°	4° 8°		
	4.06 0.00 0.51 0.30 1.14 8.38 7.30 9.65 8.00 14.60 1.78 0.90 0.00	4.06 4.57 0.00 0.10 0.51 0.81 0.30 0.407 1.14 1.30 8.38 8.69 7.30 7.80 9.65 10.16 8.00 8.62 5.08 BS 14.60 15.35 1.78 2.54 0.90 1.29 0.00 0.15 0.25 BS	

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